

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max $T_A = +25^\circ\text{C}$
20V	90mΩ @ $V_{GS} = 4.5\text{V}$	2.8A
	120mΩ @ $V_{GS} = 2.5\text{V}$	2.4A

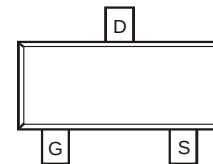
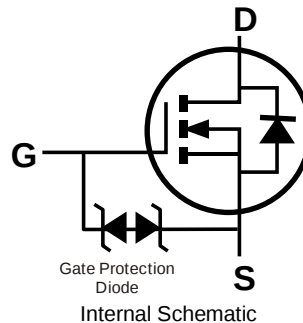
Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control



Top View



Top View

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

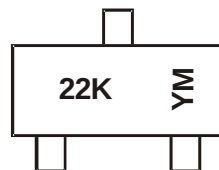
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe.
Solderable per MIL-STD-202, Method 208 (B3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMG2302UK-7	SOT23	3,000/Tape & Reel
DMG2302UK-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



22K = Product Type Marking Code
 YM = Date Code Marking
 Y or Y= Year (ex: C = 2015)
 M = Month (ex: 9 = September)

Date Code Key

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022
Code	C	D	E	F	G	H	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	2.8 2.2	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	1.1	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	12	A

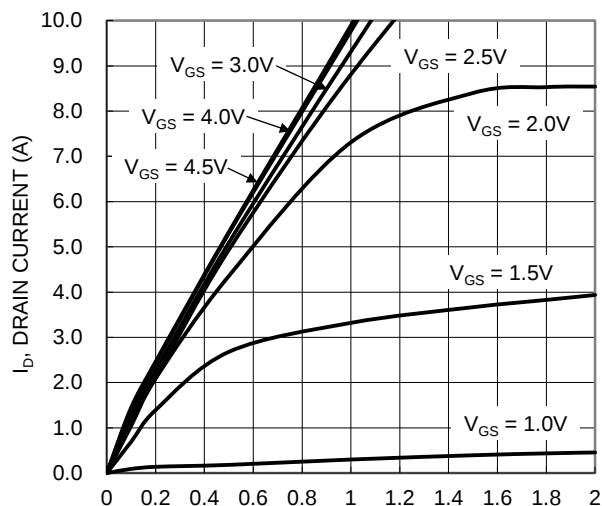
Thermal Characteristics

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)			P _D	0.66	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	192	°C/W
Total Power Dissipation (Note 6)			P _D	1.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	115	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

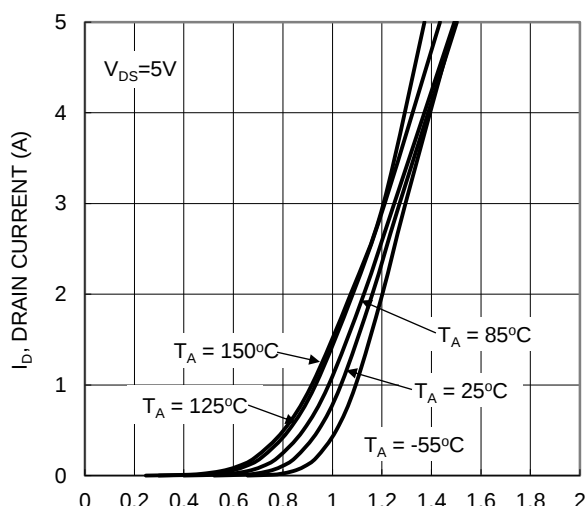
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	10	μA	V _{DS} = 16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±10V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.3	0.6	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	61	90	mΩ	V _{GS} = 4.5V, I _D = 3.6A
			80	120		V _{GS} = 2.5V, I _D = 3.1A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	130	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	26	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	18	—	pF	
Gate Resistance	R _G	—	2.7	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	1.4	—	nC	V _{DS} = 10V, I _D = 3.6A
Total Gate Charge (V _{GS} = 10V)	Q _G	—	2.8	—	nC	
Gate-Source Charge	Q _{GS}	—	0.1	—	nC	
Gate-Drain Charge	Q _{GD}	—	0.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	0.6	—	ns	V _{DS} = 10V, V _{GS} = 4.5V, R _G = 1Ω, R _L = 2.78Ω
Turn-On Rise Time	t _R	—	2.7	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	4.2	—	ns	
Turn-Off Fall Time	t _F	—	1.7	—	ns	
Reverse Recovery Time	t _{RR}	—	5.3	—	ns	I _F = 3.6A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	0.5	—	nC	I _F = 3.6A, di/dt = 100A/μs

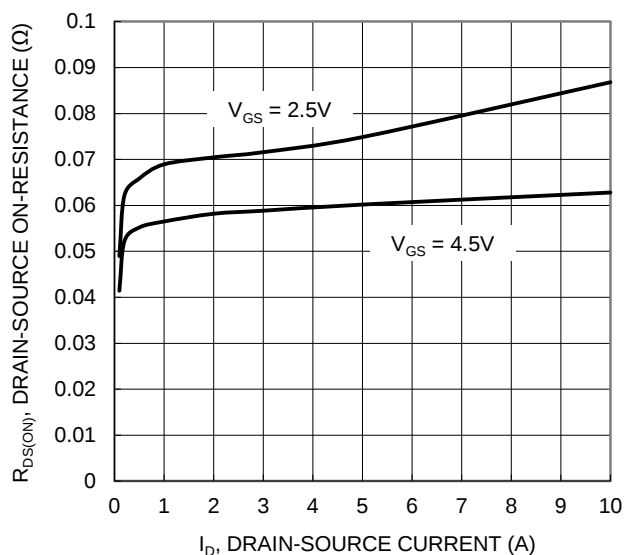
- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



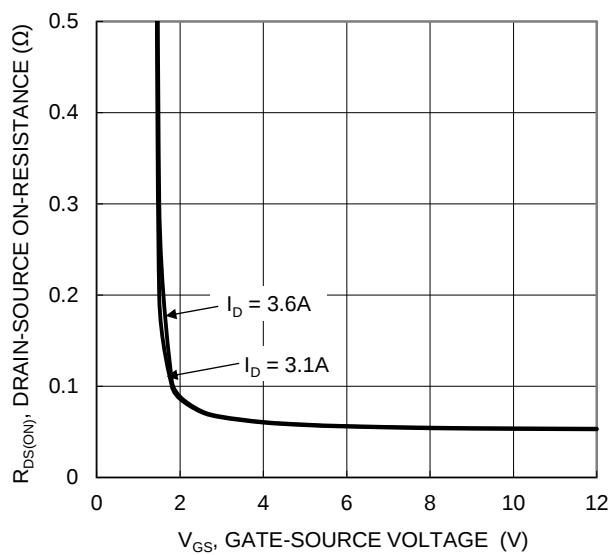
V_{DS} , DRAIN-SOURCE VOLTAGE (V)
Figure 1. Typical Output Characteristic



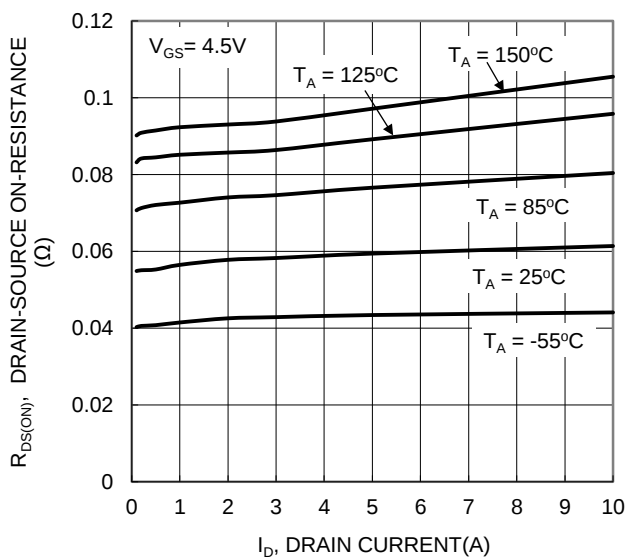
V_{GS} , GATE-SOURCE VOLTAGE (V)
Figure 2. Typical Transfer Characteristic



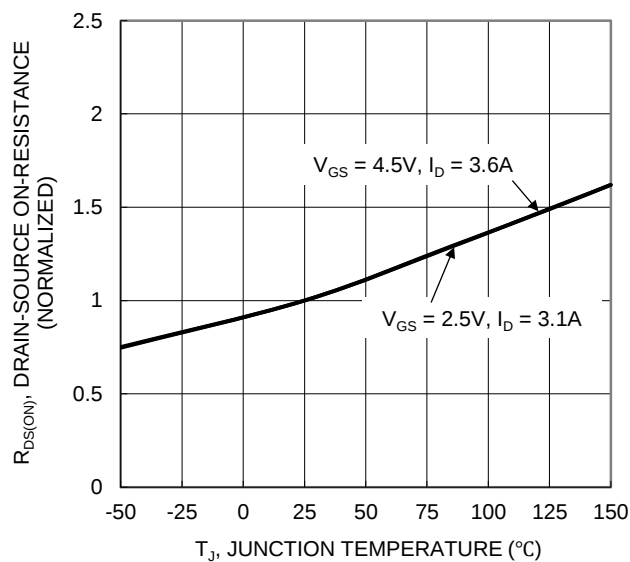
I_D , DRAIN-SOURCE CURRENT (A)
Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage



V_{GS} , GATE-SOURCE VOLTAGE (V)
Figure 4. Typical Transfer Characteristic



I_D , DRAIN CURRENT (A)
Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature



T_J , JUNCTION TEMPERATURE (°C)
Figure 6. On-Resistance Variation with Junction Temperature

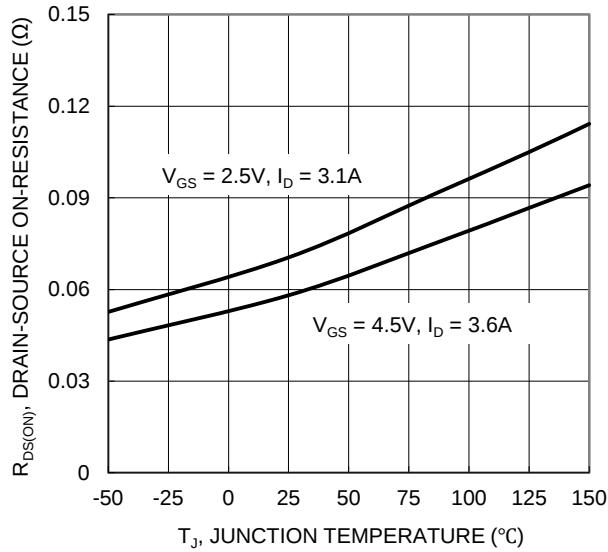


Figure 7. On-Resistance Variation with Junction Temperature

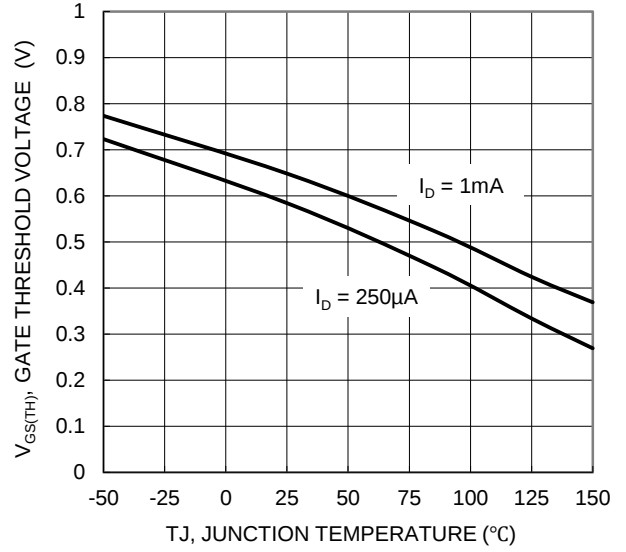


Figure 8. Gate Threshold Variation vs Junction Temperature

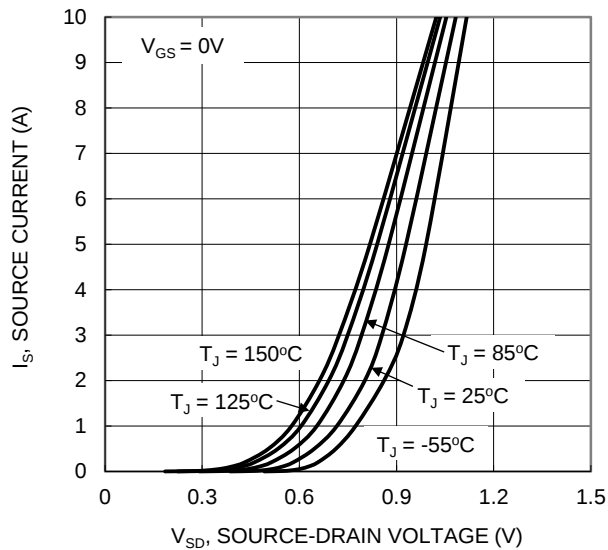


Figure 9. Diode Forward Voltage vs. Current

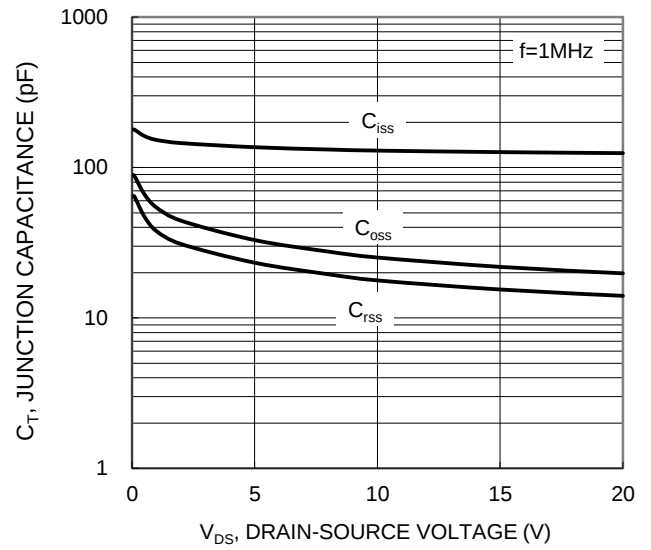


Figure 10. Typical Junction Capacitance

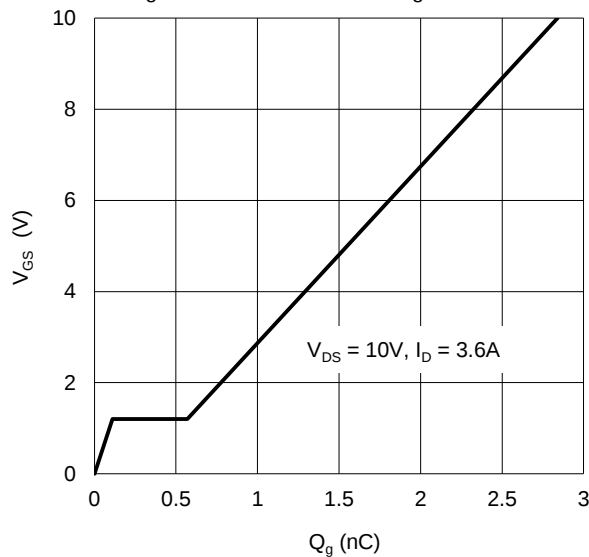


Figure 11. Gate Charge

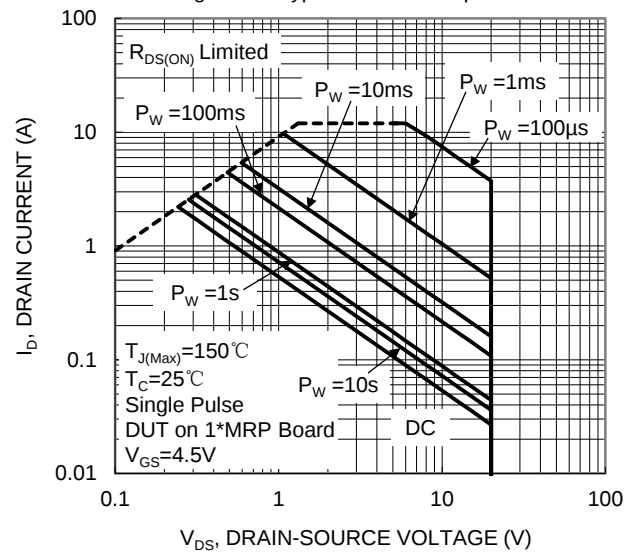


Figure 12. SOA, Safe Operation Area

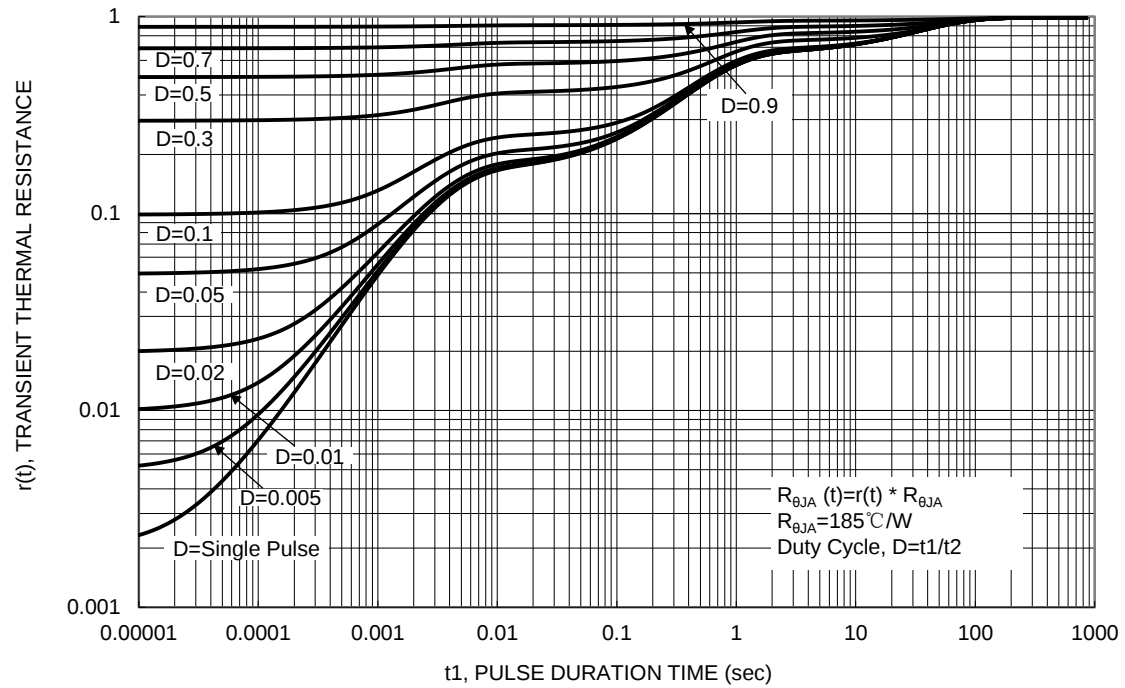
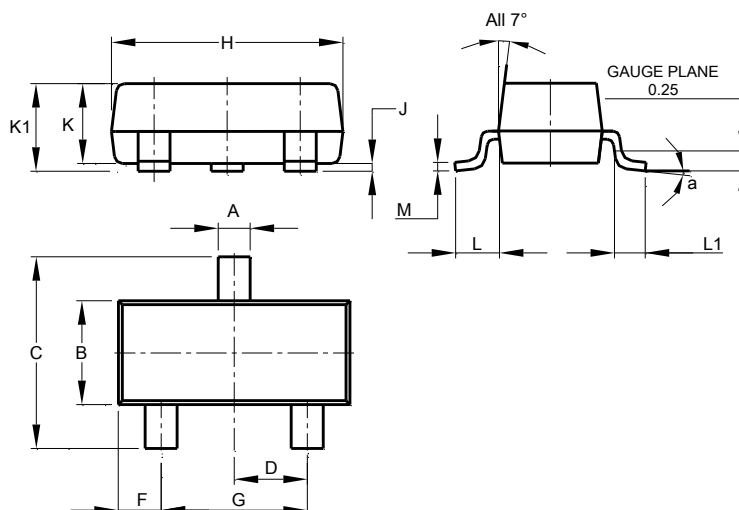


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23

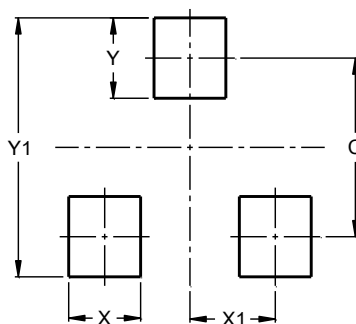


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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